

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

MTP3N100E

FEATURES

- Drain Current –I_D= 3.0A@ T_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage : V_{DSS}= 1000V(Min)
- Static Drain-Source On-Resistance
- : R_{DS(on)} = 4.0 Ω (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

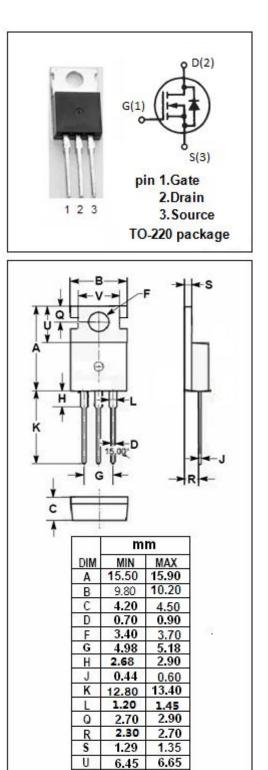
DESCRIPTION

- DC/DC Converters
- DC/AC Inverters
- Motor Drives

ABSOLUTE MAXIMUM RATINGS(Ta=25°C) SYMBOL PARAMETER VALUE UNIT VDSS **Drain-Source Voltage** 1000 V Gate-Source Voltage-Continuous V V_{GS} ± 20 Drain Current-Continuous 3.0 A Ь Drain Current-Single Pluse 9.0 A **I**DM P_{D} Total Dissipation @T_C=25℃ 125 W °C ТJ Max. Operating Junction Temperature -55~150 °C Storage Temperature -55~150 Tstg

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.0	°C/W



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8.66

8.86



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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25\,^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	1000	-	V
V _{GS(th)}	Gate Threshold Voltage	V_{DS} = V_{GS} ; I_D = 0.25mA	2.0	4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 1.5A	-	4.0	Ω
lgss	Gate-Body Leakage Current	V _{GS} = ±20V;V _{DS} = 0	-	±0.1	uA
IDSS	Zero Gate Voltage Drain Current	V _{DS} = 1000V; V _{GS} = 0	-	10	μA
V _{SD}	Forward On-Voltage	I _S = 3.0A; V _{GS} = 0	-	1.1	V

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